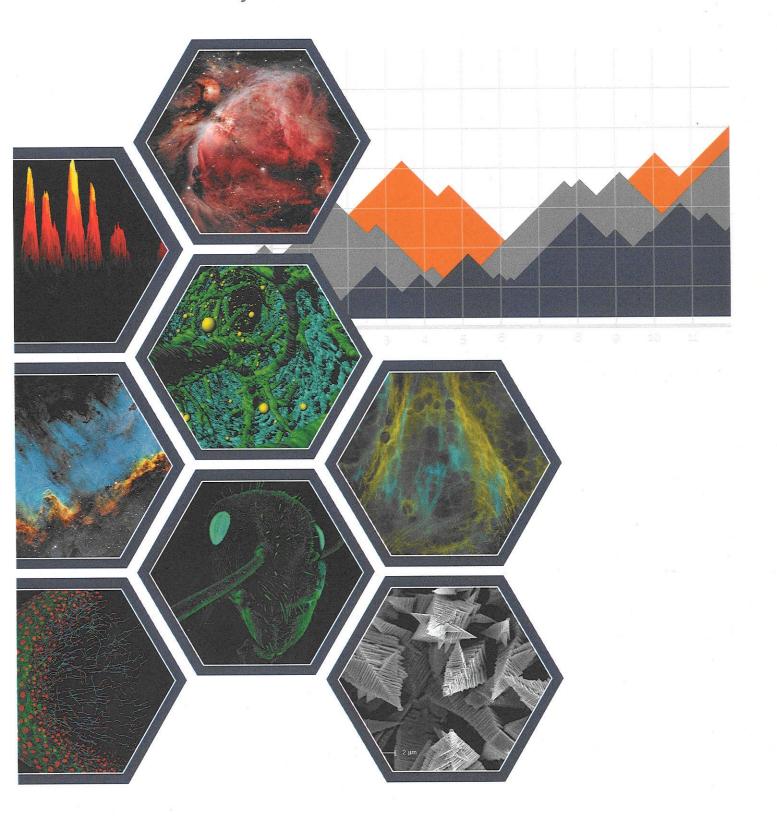


# System Performance Booklet





### System Overview

Description	Model			Ser	ial N	umber	
CCD Head V	D U 9	40P	- BV	CC	D-21	1642	
TE Cooler performance	(*)	13.11		High		Ultra-high	· WARE
Accessories	Power Su	pply Un	it PS -2	24		PS -25	•
3 340.00	SO-	LM-	Clevines asig	MF	L-		
Serial/Batch Number			1.1				2
Other			4.7		. 8		- 13 - 13

Sensor types are defined in Table 1 using the last two letters in box Model Number.

#### **CCD Details**

Manufac	turer / Model No.	Pixels	Serial Number	
E2V	CCD207-10	1600x400, 16μm x 16μm	FX	24.4
E2V	CCD207-00	1600x200, 16μm x 16μm	SX.	25.4
E2V	CCD42-10	2048x512, 13.5μm x 13.5μm	14441-04-18	80.0
E2V	CCD30-11	1024x256, 26μm x 26μm		

Special Feature	(*)	(*)
NIMO	Other (specify)	
Fringe Suppression	Custom Cables	
Shielded Anti-Blooming	To all a	

Window Variant	(*)		(~)
VUV-UV Parallel	T.	NUV-Enhanced Parallel	
Broadband VUV-NIR Wedged		Broadband VUV-NIR Parallel	
Broadband VIS-NIR Wedged	3	Broadband VIS-NIR Parallel	
VIS-NIR Enhanced Wedged		Bose-Einstein 780nm Wedged	
None	JAN 12 10 10 10 10 10 10 10 10 10 10 10 10 10	Other	

## System Sensitivity •1

A/D Rate (MHz All 16 bit)	Preamp setting	High Sensitivity (HS) Output eles per A/D count	High Capacity (HC) Output eles per A/D count
3	x1	4.1	18.7
3	x2	2.1	9.7
3	x4	1.0	4.8
1.0	x1	4.2	19.7
1.0	x2	2.2	9.8
1.0	x4	1.0	4.9
0.05	x1	4.3	19.1
0.05	x2	2.2	10.0
0.05	x4	1.0	5.0

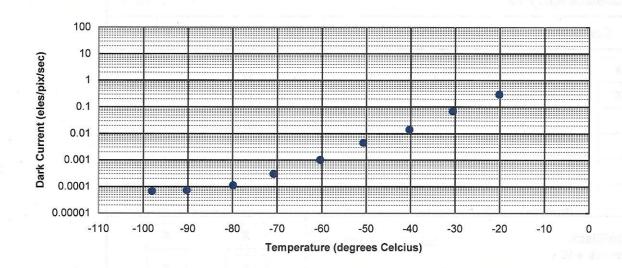
### **Summary of System Test Data**

### Readout Noise #2 and Base Mean Level

A/D Rate (MHz All 16 bit)	Output Amplifier	Single Pixel Noise electrons	Full Vert Bin Noise electrons	Base Level #3 (Counts)
3	HS	10.1	9.9	2639
3	HC	39.5	37.1	865
1.0	HS	6.8	6.7	991
1.0	HC	28.0	27.0	733
0.05	HS	3.4	3.6	601
0.05	HC	9.9	9.7	567
Saturation	Signal per pi	xel 10	6439 Electror	ns/pixel



#### **CCD Dark Current**



Minimum Dark Current Achievable ◆4	0.000067	elect	rons/pixel/	sec
@ Sensor Temperature of •5	-90.068	°C	16.0	°C cooling water
parties and the control of the contr		With I	PS-25	
CCD Dark Current Uniformity better than ◆6	0.0016	elect	rons/pixel/	sec

### **Linearity and Uniformity**

Linearity better than ◆7	1	% over 16 bits	
Response Uniformity better than ♦8	1.65	%	



#### **Response Defects**

Centroid	Number of Pixels	Centroid	Number of Pixels
	X	( , ) ( , ) ( , ) ( , ) ( , )	
White/Black Columns ◆10	Column numb	pers indicated X	
Trap ♦11		(X,Y) ( X	. X )

#### **Dark Current Defects**

	Number of Pixels	Centroid	Number of Pixels	Centroid
1			X	(XXX)
		, , )		1/
		( )	X	( X , X )
Med pinceri.	7. 6. ESS.	( , )		,
vil severeli		( , )		, , )
te de la companio de		( , , )		, , ,
		( , )		(

### **Test Conditions**

Readout Noise tested at	-80	°C with	16	°C water
Base Mean Level measured at	-80	°C with	16	°C water
Dark Current Uniformity tested at	-50	°C with	16	°C water
Blemishes tested at	-50	°C with	16	°C water



**Additional Comments** 

System Passed for Shipping

Signed

Date

K.MCDOWELL

31ST JANUARY 2018

 Hardware
 System Configuration
 FPGA

 Version #
 AE
 20.24

 Shipping Software Version #
 Solis SDK

 Version #
 4.30.30034.0
 2.102.30034.0

Testing

Software

Solis SDK

Version # 4.30.30034.0 2.102.33034.0

# abla Table 1; Key code to define the meanings of the last two letters in the Model Number

		Sensor Options	
OE	Open electrode	BU2	Back Illuminated (BI) + 250nm UV optimised
FI	Front illuminated (FI)	BU	BI + UV (350nm) optimised
UV	FI+UV coating	BV	BI + VIS (550nm) optimised)
FO	FI + Fibre optic	BR-DD	BI + NIR +deepdepletion
FI-DD	FI + deep depletion	BN	BI with no AR coating



#### **Performance Notes**

- Readout Noise is measured for both single pixel (SP) and fully vertically binned (FVB) with the CCD in darkness at temperature indicated and minimum exposure time. Noise values will change with pre-amplifier gain selection [PAG].
- Average electronic DC offset for CCD in darkness at temperature indicated and minimum exposure time under dark conditions measured by single pixel (SP) for imaging systems and by (FVB) for spectroscopic systems.
- ♦3 Sensitivity is calculated in photoelectrons per A/D count from measurements of the Photon Transfer Curve.
- Dark current falls exponentially with temperature. However, for a given temperature the actual dark current can vary by more than an order of magnitude from device to device. The devices are specified in terms of minimum dark current achievable rather than minimum temperature.
- ♦5 Minimum temperature achieved for thermoelectric (TE) cooler set to maximum value with water cooling
- RMS (root mean square) deviation of dark current for fully binned operation for spectroscopic cameras, or full resolution image for imaging cameras, under dark conditions at temperature indicated (pixel/column defects not included). This variation is mainly cosmetic since it is fully subtractable without significant loss of performance.
- ♦7 Linearity is measured from a plot of Counts vs. Signal over the 16 bit dynamic range. Linearity is expressed as a %age deviation from a straight line fit. This quantity is not measured on individual systems.
- ♦8 RMS (root mean square) deviation from the average response of the CCD in fully binned operation for spectroscopic cameras illuminated with uniform white light (defects not included).
- ♦9 White/black pixels have signals >25% above/below the average (25% contrast) with uniform illumination across the sensor.
- ◆10 Columns whose signals have >10% contrast in binned operation with uniform illumination across the sensor for spectroscopic cameras.
- ♦11 Pixels which absorb charge as it is clocked through the defective area. When the light source is switched off, the signal from the trap appears to drop off more slowly than the signal from the surrounding pixels.
- ♦12 Hot spots are counted if they exhibit >50 times the maximum specified dark current at the test temperature indicated.
- ♦ 13 A column is considered defective if >10 pixels are affected, or if the column exhibits >2 times the maximum specified dark current at the test temperature indicated.